

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2N5190 2N5191 2N5192

DESCRIPTION

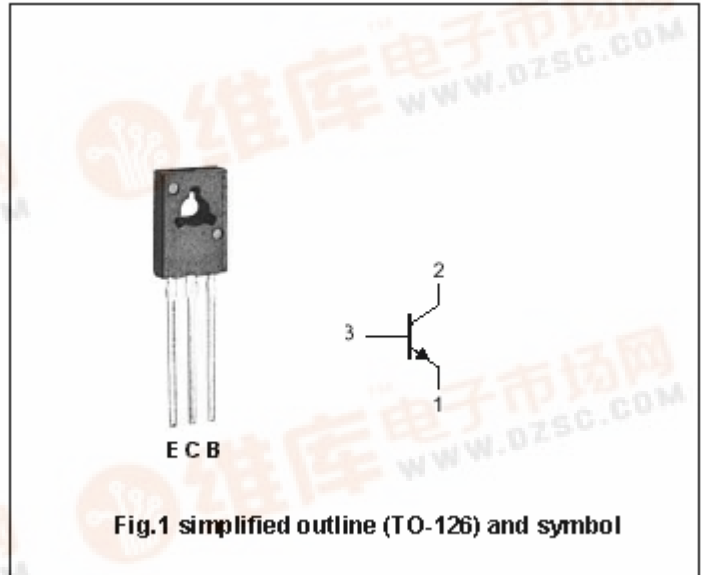
- With TO-126 package
- Complement to type 2N5193/5194/5195
- Excellent safe operating area

APPLICATIONS

- For use in medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N5190	40	V
		2N5191	60	
		2N5192	80	
V _{CEO}	Collector-emitter voltage	2N5190	40	V
		2N5191	60	
		2N5192	80	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		4	A
I _{CM}	Collector current-Peak		7	A
I _B	Base current		1	A
P _D	Total power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	3.12	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N5190	I _C =0.1A; I _B =0	40			V
		2N5191		60			
		2N5192		80			
V _{CEsat-1}	Collector-emitter saturation voltage		I _C =1.5A; I _B =0.15A			0.6	V
V _{CEsat-2}	Collector-emitter saturation voltage		I _C =4A; I _B =1A			1.4	V
V _{BE}	Base-emitter on voltage		I _C =1.5A; V _{CE} =2V			1.2	V
I _{CEO}	Collector cut-off current	2N5190	V _{CE} =40V; I _B =0			1.0	mA
		2N5191	V _{CE} =60V; I _B =0				
		2N5192	V _{CE} =80V; I _B =0				
I _{CBO}	Collector cut-off current	2N5190	V _{CB} =40V; I _E =0			0.1	mA
		2N5191	V _{CB} =60V; I _E =0				
		2N5192	V _{CB} =80V; I _E =0				
I _{CEX}	Collector cut-off current	2N5190	V _{CE} =40V; V _{BE(off)} =1.5V T _C =125			0.1 2.0	mA
		2N5191	V _{CE} =60V; V _{BE(off)} =1.5V T _C =125			0.1 2.0	
		2N5192	V _{CE} =80V; V _{BE(off)} =1.5V T _C =125			0.1 2.0	
I _{EBO}	Emitter cut-off current		V _{EB} =5V; I _C =0			1.0	mA
h _{FE-1}	DC current gain	2N5190	I _C =1.5A; V _{CE} =2V	25		100	
		2N5191					
		2N5192		20	80		
h _{FE-2}	DC current gain	2N5190	I _C =4A; V _{CE} =2V	10			
		2N5191					
		2N5192		7			
f _T	Transition frequency		I _C =1A; V _{CE} =10V; f=1MHz	2			MHz

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PACKAGE OUTLINE

